

Discrete IGBTs Silicon N-Channel IGBT

GT15J341

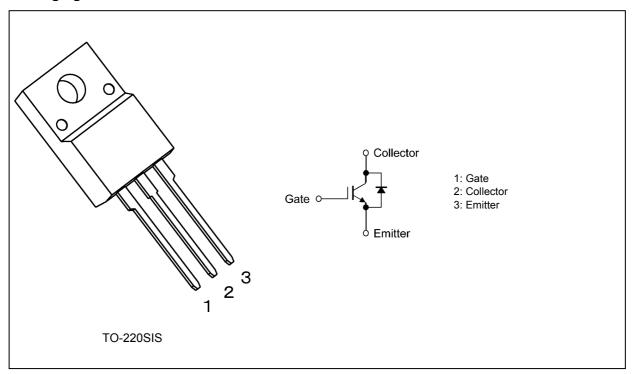
1. Applications

· Motor Drivers

2. Features

- (1) Sixth generation
- (2) Low saturation voltage: $V_{CE(sat)} = 1.5 \text{ V (typ.)}$ ($I_C = 15 \text{ A}$)
- (3) FRD included between emitter and collector

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25°C, unless otherwise specified)

Characteristics				Rating	Unit
Collector-emitter voltage			V _{CES}	600	V
Gate-emitter voltage			V_{GES}	±25	
Collector current (DC)	(T _c = 25°C)		I _C	15	Α
Collector current (DC)	(T _c = 100°C)		Ic	8	
Collector current (pulsed)			I _{CP}	60	
Diode forward current (DC)	(T _c = 25°C)		I _F	15	
Diode forward current (DC)	(T _c = 100°C)		I _F	7	
Short circuit withstand time		(Note 1)	t _{sc}	5	μS
Collector power dissipation	(T _c = 25°C)		Pc	30	W
Junction temperature			Tj	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

In general, loss of IGBT increases more when it has positive temperature coefficient and gets higher temperature.

In case that the temperature rise due to loss of IGBT exceeds the heat release capacity of a device, it leads to thermorunaway and results in destruction.

Therefore, please design heat release of a device with due consideration to the temperature rise of IGBT.

Note 1: V_{CC} = 300 V, V_{GG} = +15 V/0 V, $T_j \le$ 125°C

5. Thermal Characteristics

Characteristics		Max	Unit
Junction-to-case thermal resistance (IGBT)		4.16	°C/W
Junction-to-case thermal resistance (diode)		4.63	

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C, unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GES}	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0 \text{ V}$	_	_	±100	nA
Collector cut-off current	I _{CES}	V _{CE} = 600 V, V _{GE} = 0 V	_	_	100	μА
Gate-emitter cut-off voltage	V _{GE(OFF)}	I _C = 1.5 mA, V _{CE} = 5 V	3.5	5.5	6.5	V
Collector-emitter saturation voltage	V _{CE(sat)}	I_C = 15 A, V_{GE} = 15 V, T_c = 25°C	_	1.5	2.0	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 15 A, V _{GE} = 15 V, T _c = 125°C	_	1.8	_	
Diode forward voltage	V _F	I _F = 15 A, V _{GE} = 0 V, T _c = 25°C		1.4	2.0	
Diode forward voltage	V _F	I _F = 15 A, V _{GE} = 0 V, T _c = 125°C	_	1.2	_	



6.2. Dynamic Characteristics (T_a = 25°C, unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{ies}	V _{CE} = 10 V, V _{GE} = 0 V, f = 100 kHz	_	1390	_	pF
Switching time (turn-on delay time)	t _{d(on)}	Inductive load	_	0.06	_	μS
Switching time (rise time)	t _r	V_{CC} = 300 V, I_{C} = 15 A, V_{GG} = +15 V/0 V, R_{G} = 33 Ω	_	0.03	_	
Switching time (turn-on time)	t _{on}	$ T_c = 25^{\circ}C$,	_	0.14	_	
Switching time (turn-off delay time)	t _{d(off)}	See Fig. 6.2.1, 6.2.2, 6.2.3	_	0.17	_	
Switching time (fall time)	t _f		_	0.08	_	
Switching time (turn-off time)	t _{off}		_	0.28	_	
Switching loss (turn-on switching loss)	E _{on}		_	0.3	_	mJ
Switching loss (turn-off switching loss)	E _{off}		_	0.3	_	
Switching time (turn-on delay time)	t _{d(on)}	Inductive load $V_{CC} = 300 \text{ V, } I_{C} = 15 \text{ A,} \\ V_{GG} = +15 \text{ V/0 V, } R_{G} = 33 \Omega \\ T_{c} = 125^{\circ}\text{C,} \\ \text{See Fig. 6.2.1, 6.2.2, 6.2.3}$	_	0.06	_	μS
Switching time (rise time)	t _r		_	0.04	_	
Switching time (turn-on time)	t _{on}		_	0.18	_	
Switching time (turn-off delay time)	t _{d(off)}		_	0.18	_	
Switching time (fall time)	t _f		_	0.11	_	
Switching time (turn-off time)	t _{off}		_	0.32	_	
Switching loss (turn-on switching loss)	E _{on}		_	0.5	_	mJ
Switching loss (turn-off switching loss)	E _{off}		_	0.3	_	
Reverse recovery time	t _{rr}	I _F = 15 A, di/dt = -100 A/μs	_	80		ns

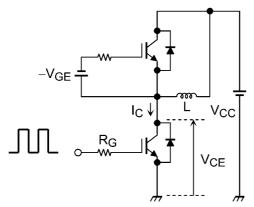


Fig. 6.2.1 Test Circuit of Switching Time

Fig. 6.2.2 Timing Chart of Switching Time

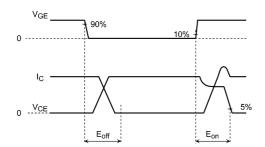


Fig. 6.2.3 Timing Chart of Switching Loss

Rev.2.0



7. Marking (Note)

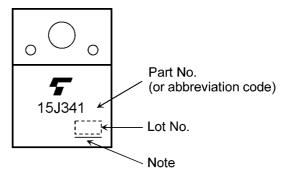


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

8. Characteristics Curves (Note)

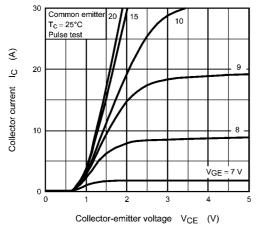
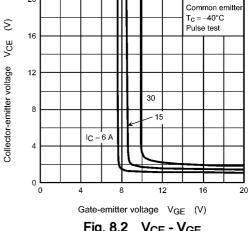


Fig. 8.1 I_C - V_{CE}



20

Fig. 8.2 V_{CE} - V_{GE}

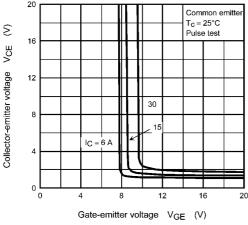


Fig. 8.3 V_{CE} - V_{GE}

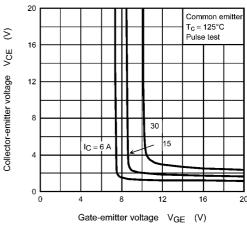
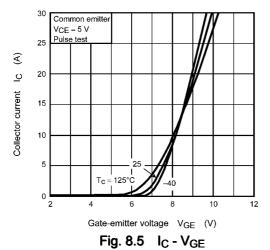


Fig. 8.4 V_{CE} - V_{GE}



Common emitter VGE = 15 V Collector-emitter saturation voltage VCE (sat) (V) Pulse test 30 A 15 A IC = 6 A 40 -20 20 80 Case temperature T_C (°C)

Fig. 8.6 V_{CE(sat)} - T_c

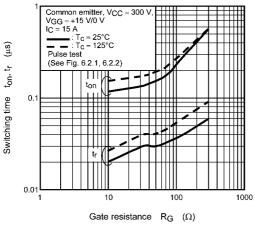
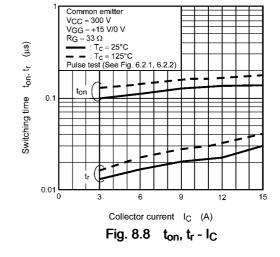


Fig. 8.7 t_{on} , t_r - R_G



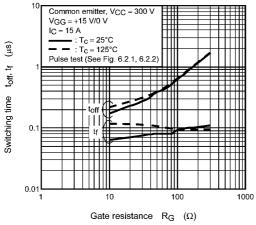


Fig. 8.9 toff, tf - RG

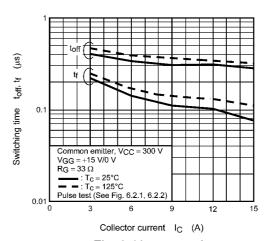


Fig. 8.10 t_{off}, t_f - I_C

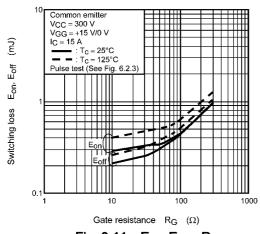


Fig. 8.11 E_{on}, E_{off} - R_G

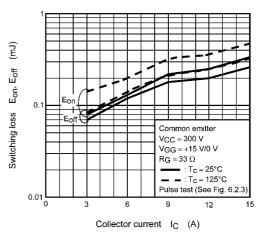


Fig. 8.12 Eon, Eoff - IC

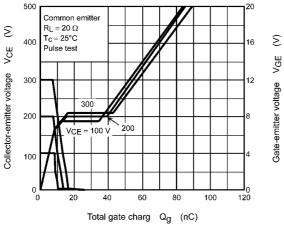


Fig. 8.13 V_{CE}, V_{GE} - Q_g

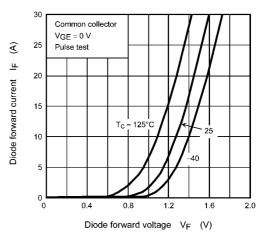


Fig. 8.14 I_F - V_F

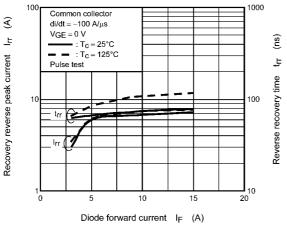


Fig. 8.15 I_{rr}, t_{rr} - I_F

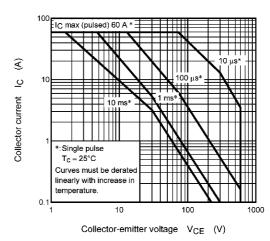


Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

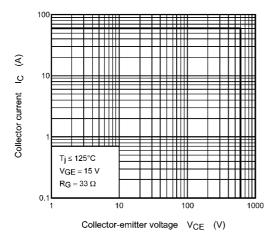
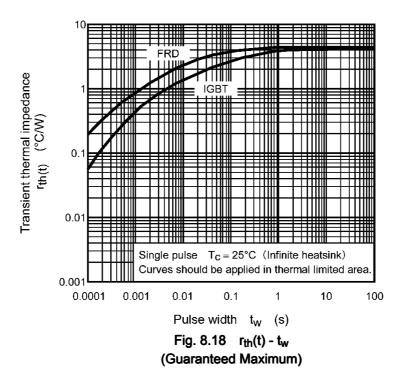


Fig. 8.17 Reverse Bias SOA (Guaranteed Maximum)

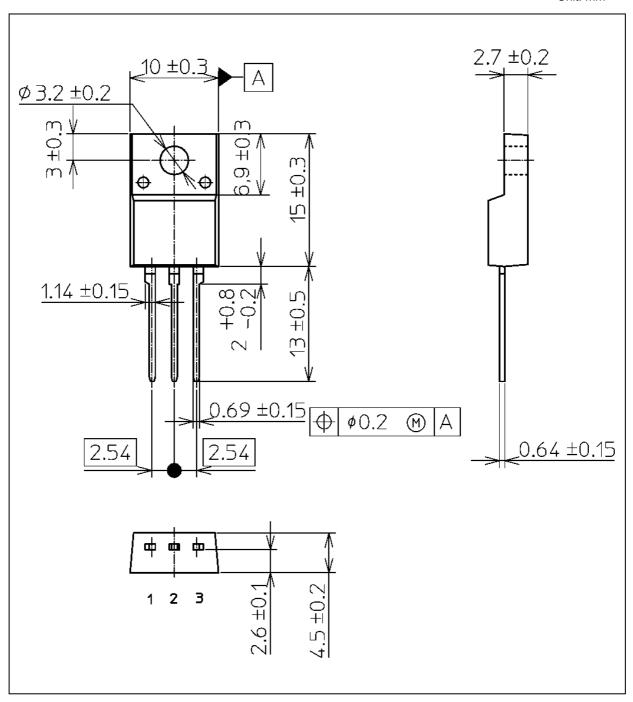


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.7 g (typ.)

	Package Name(s)
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	



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